

Growth of Gray Tin epilayers on insulating (001)-CdTe/GaAs substrates and its

Angular Resolved Photoemission Spectroscopy studies

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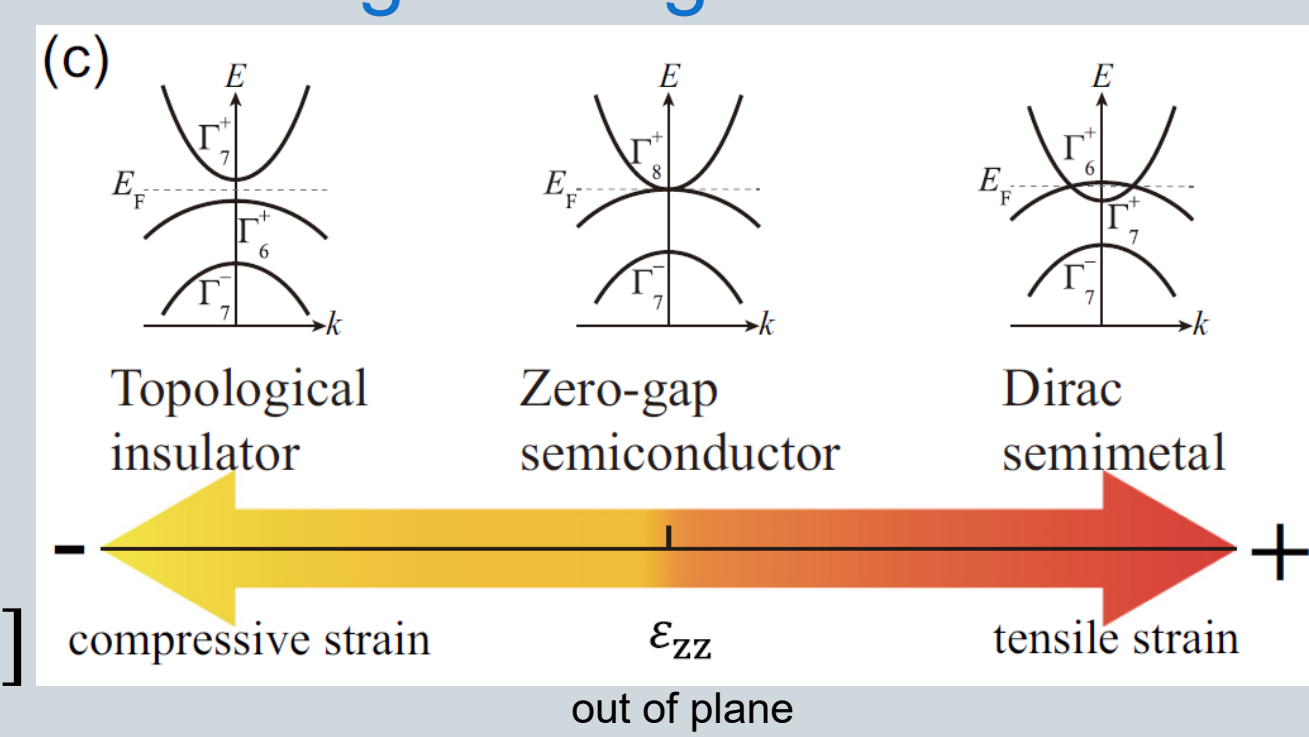
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Introduction & Motivation

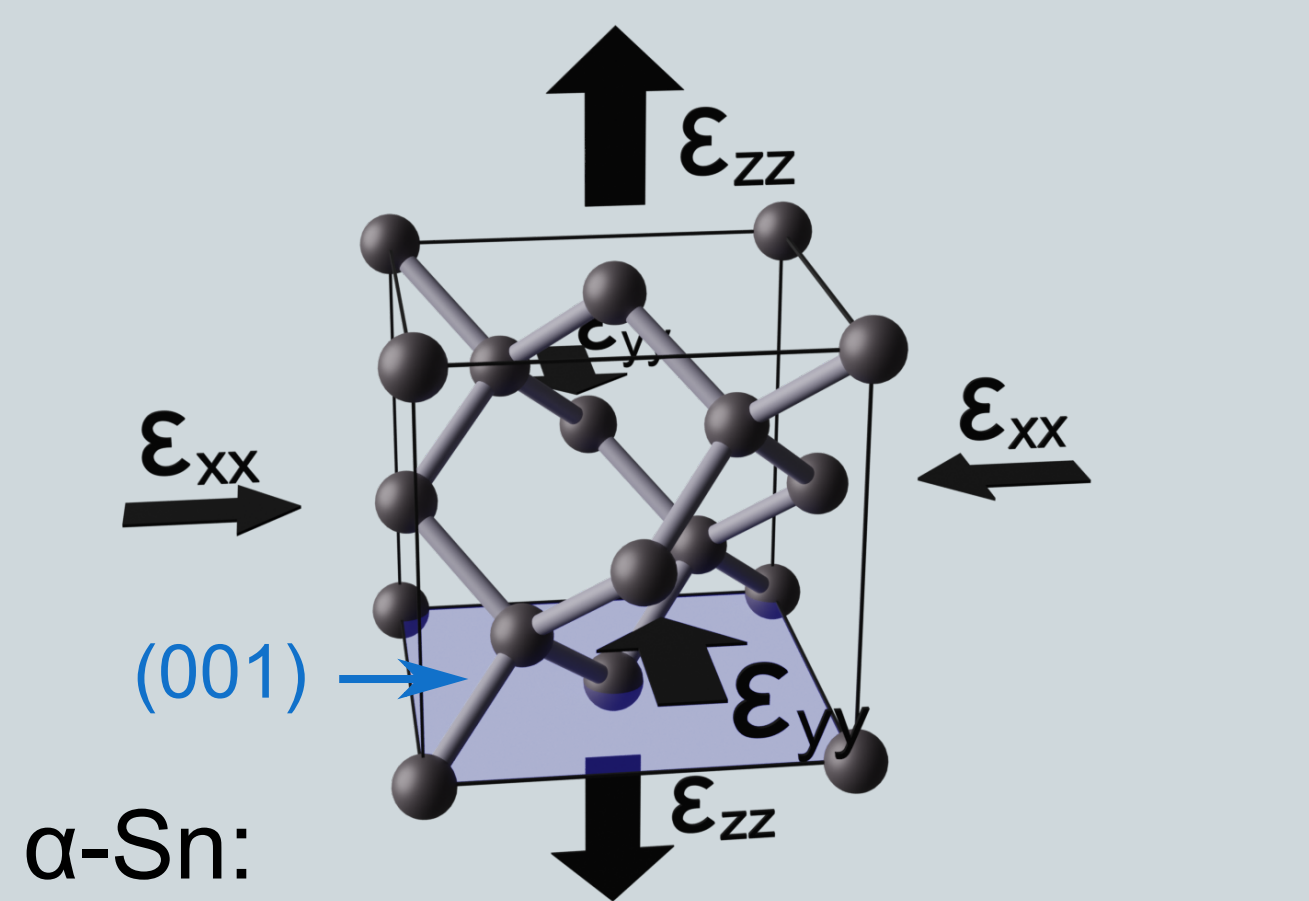
Fundamental point

Phase transitions realized by strain engineering



[5] compressive strain ϵ_{zz} tensile strain

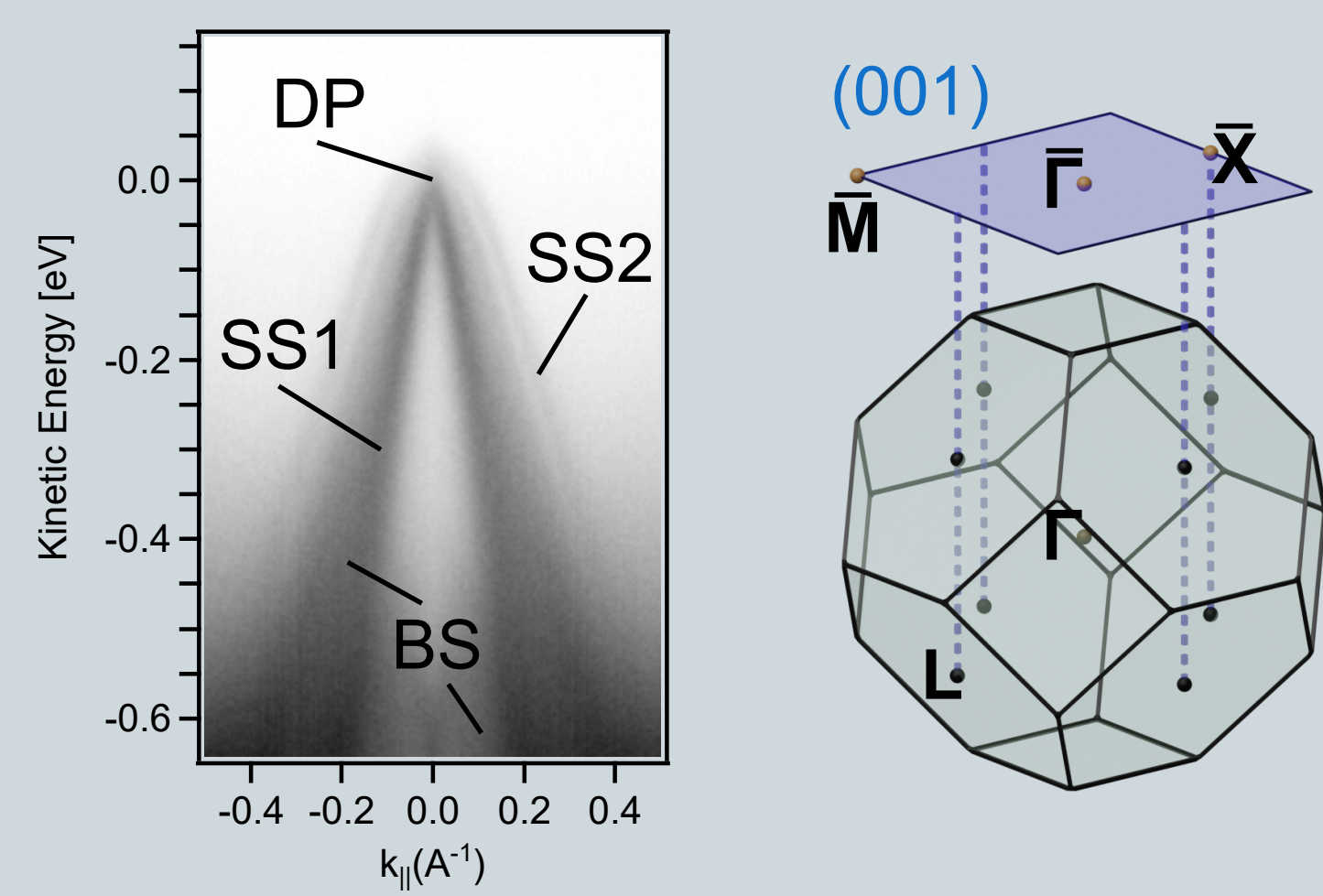
tensile strain $\epsilon_{xx}, \epsilon_{yy}$ compressive strain



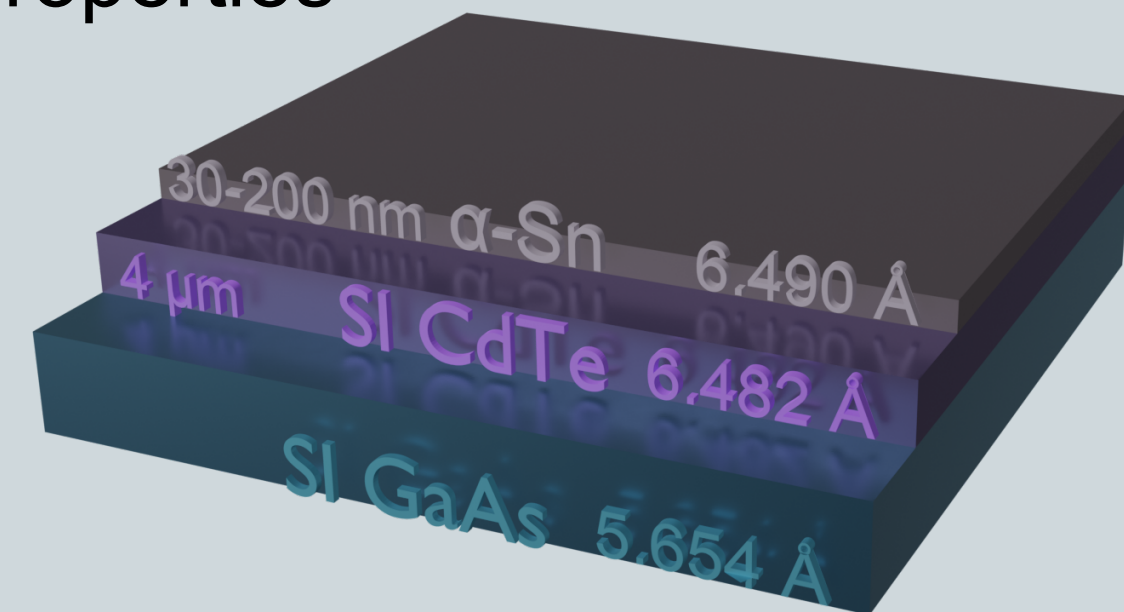
α -Sn:
Diamond cubic structure
Compressive in-plane strain

Transport measurements in external magnetic field

- breaks time-reversal symmetry \rightarrow Weyl semimetal
- induces chiral anomaly in \vec{B} parallel to current



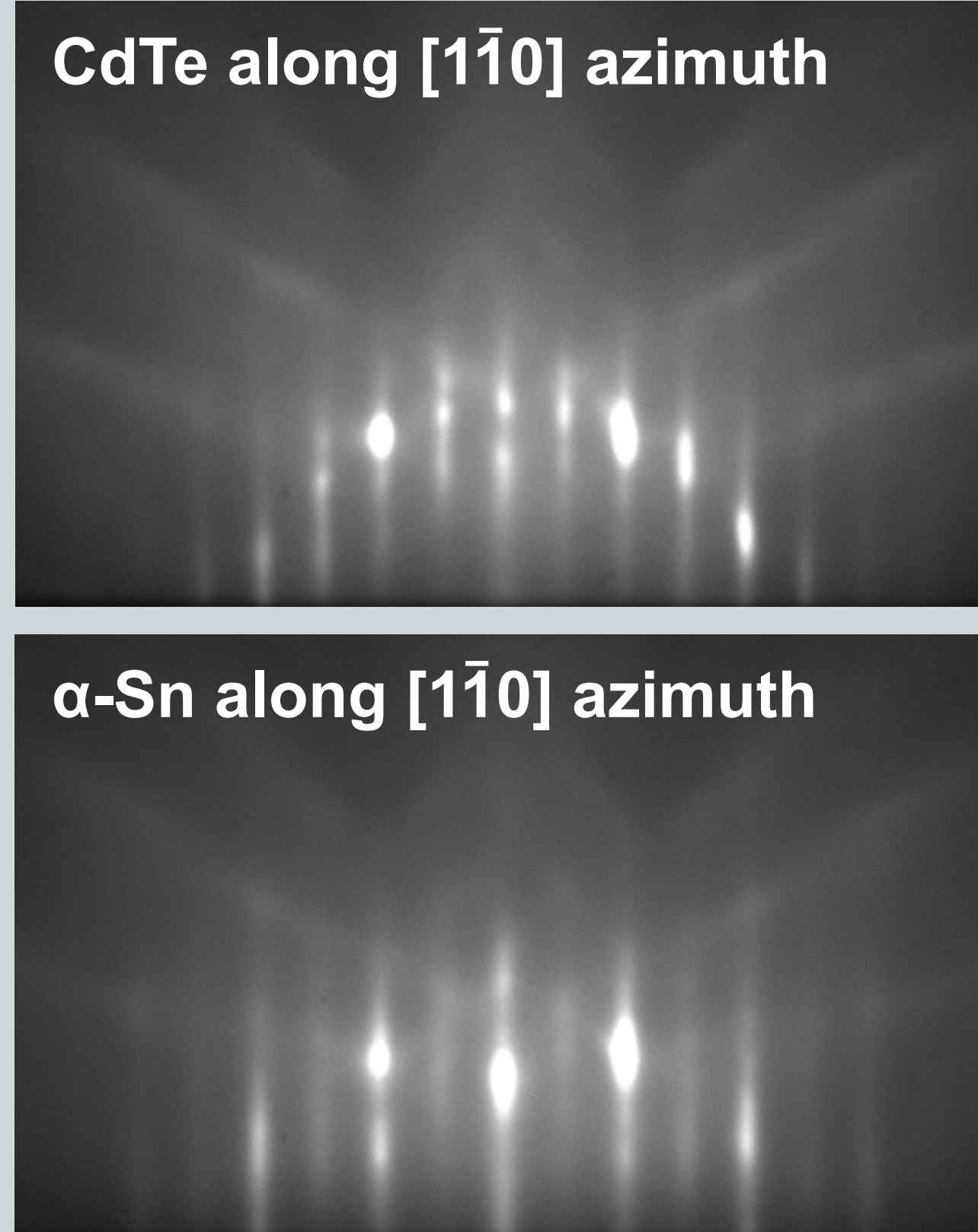
MBE growth on semi insulating (SI) substrates to study transport properties



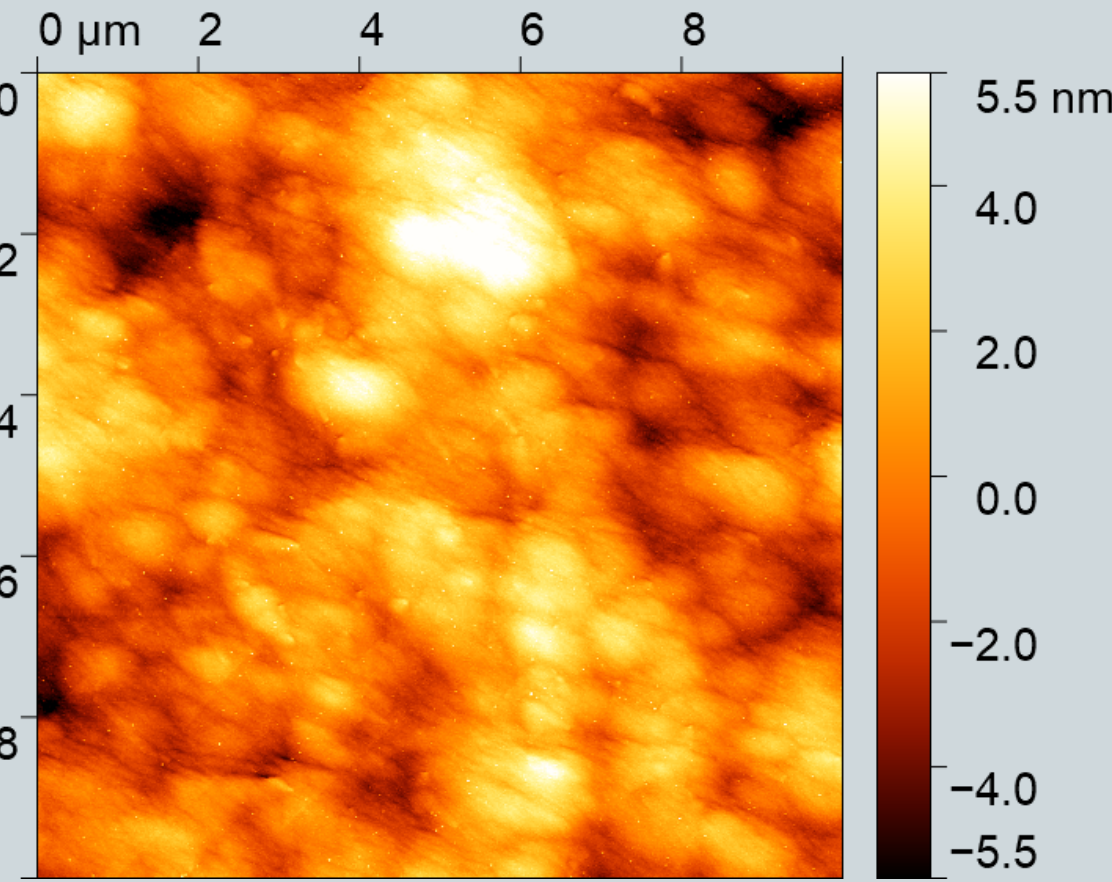
Compressive in-plane strain **-0.1%** due to lattice mismatch

MBE growth of thin α - Sn films

RHEED



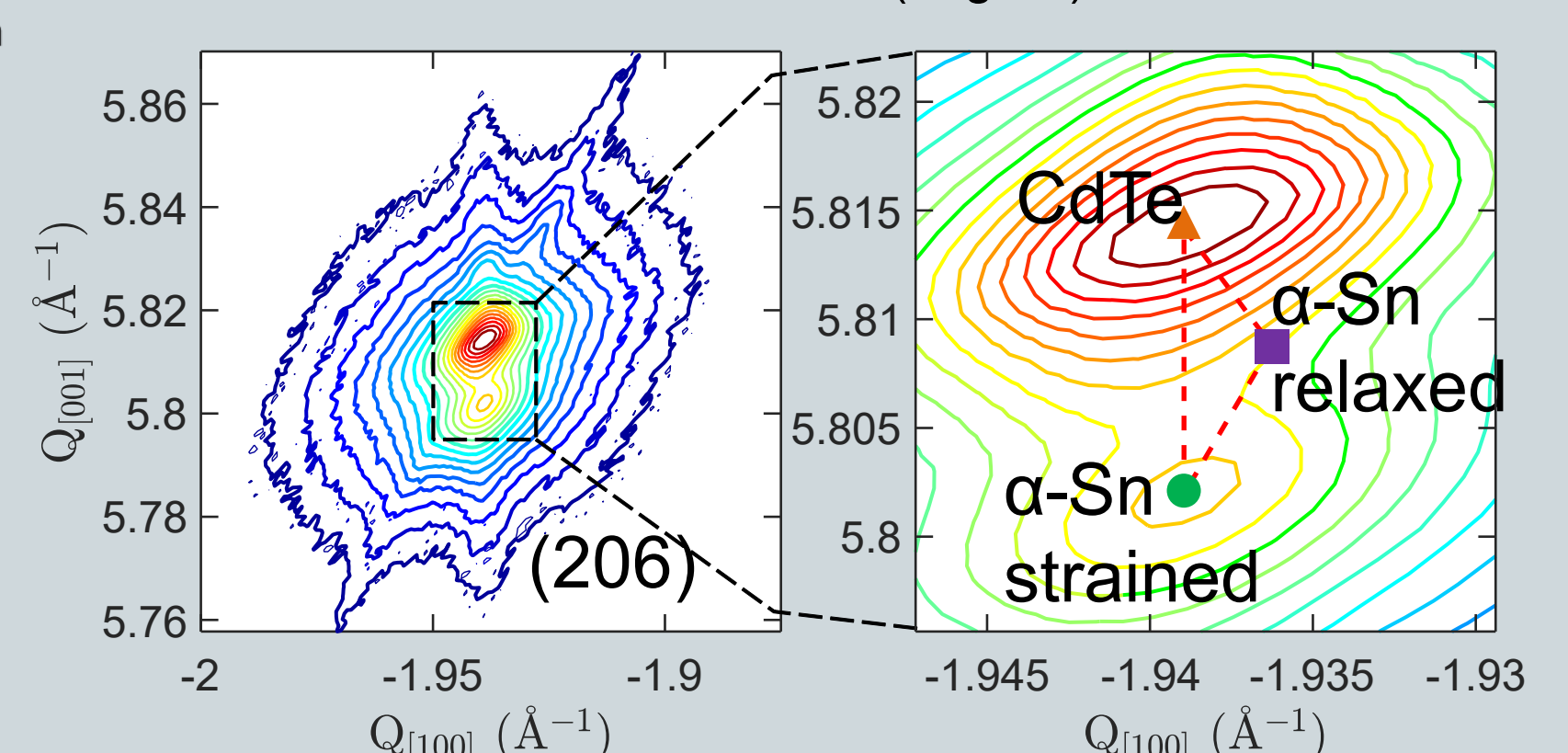
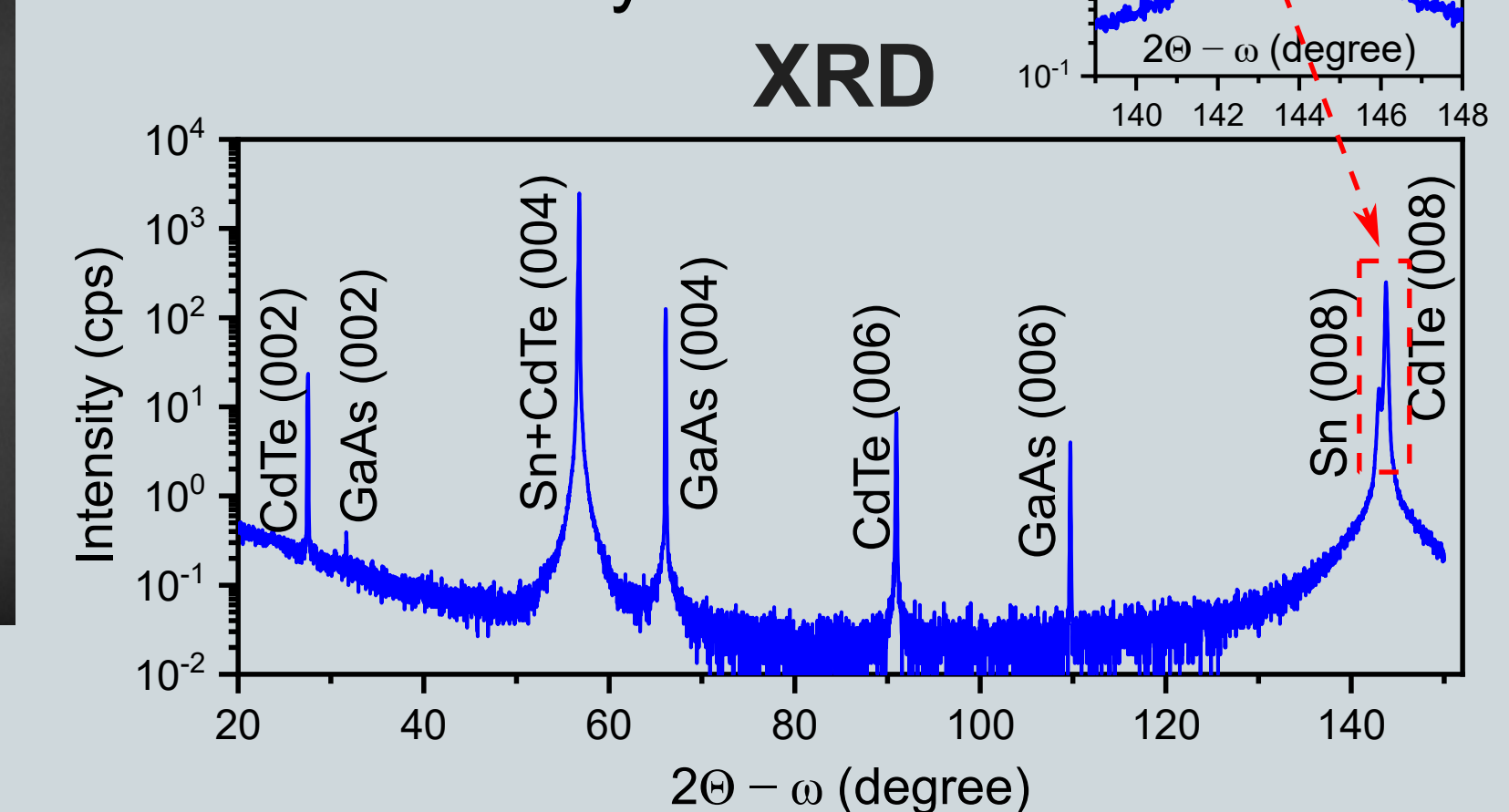
AFM RMS = 2 nm



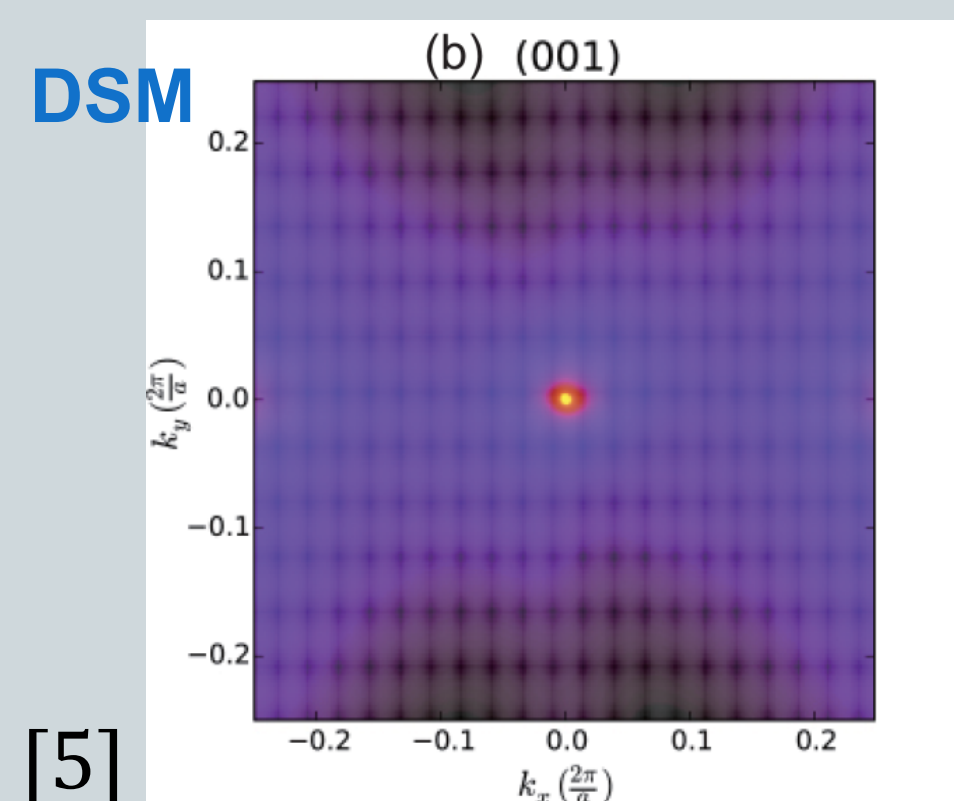
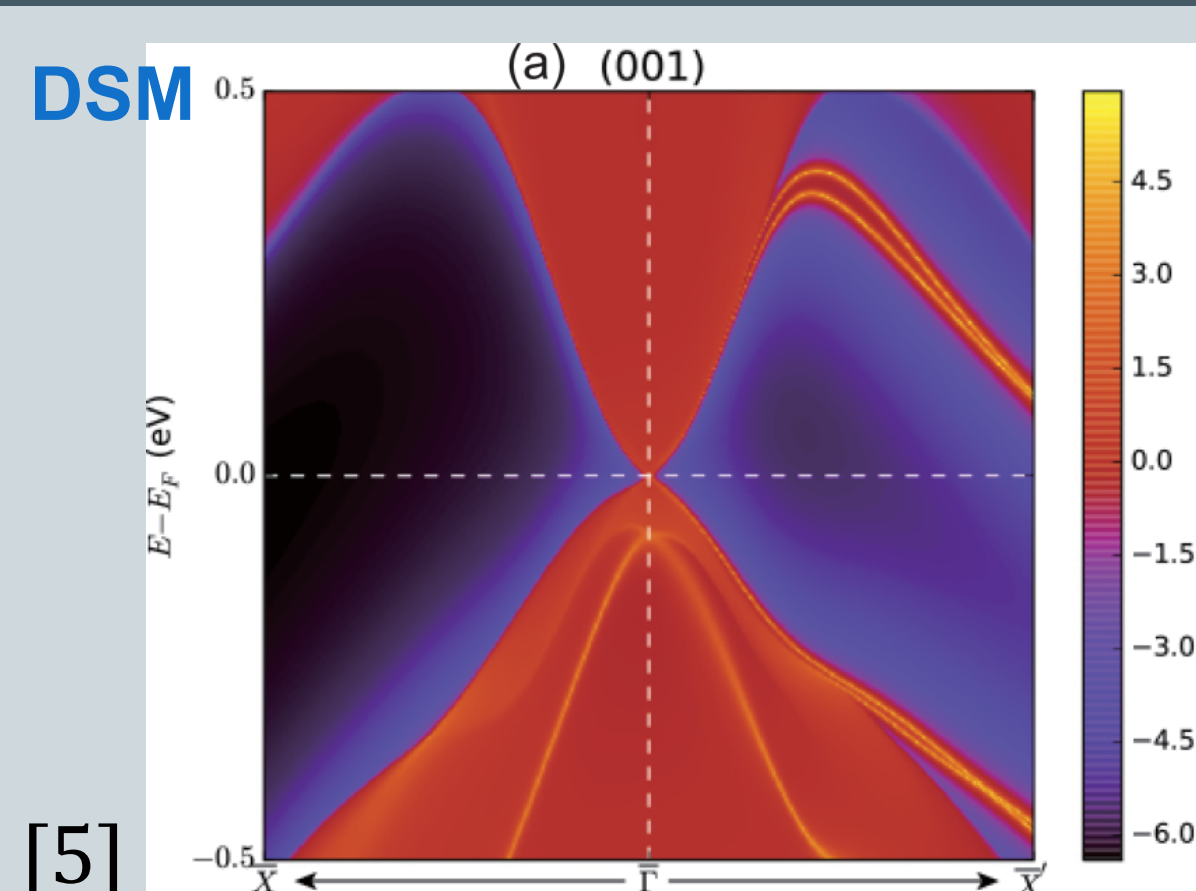
Conditions

- MBE growth below RT
- Bulk α -Sn stable only below **13.2°C**
- α -Sn thin epitaxial film stable above RT [2]

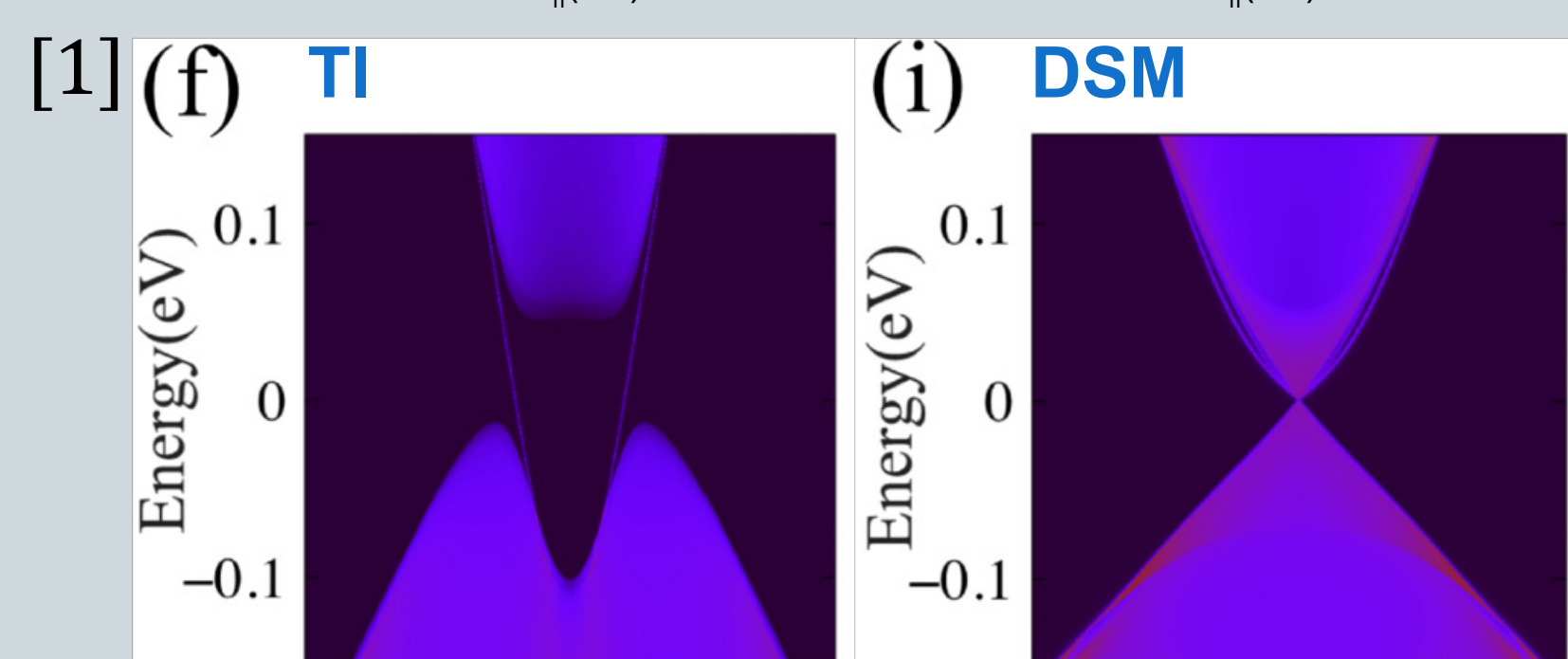
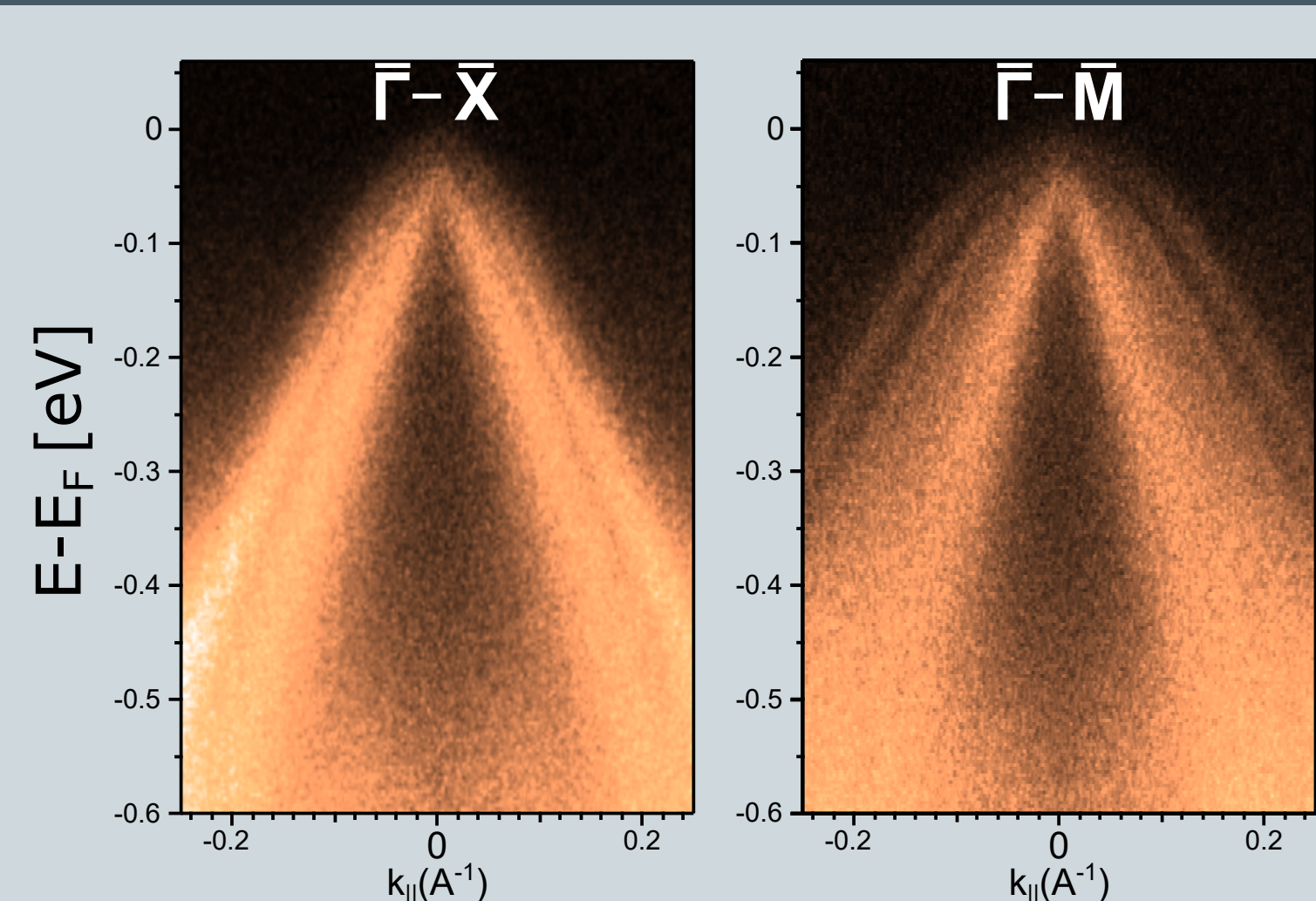
α -Sn XRD for (001) orientation present only at (00X) planes, where X is divisible by 4.



Angular Resolved Photoemission Spectroscopy (ARPES) results

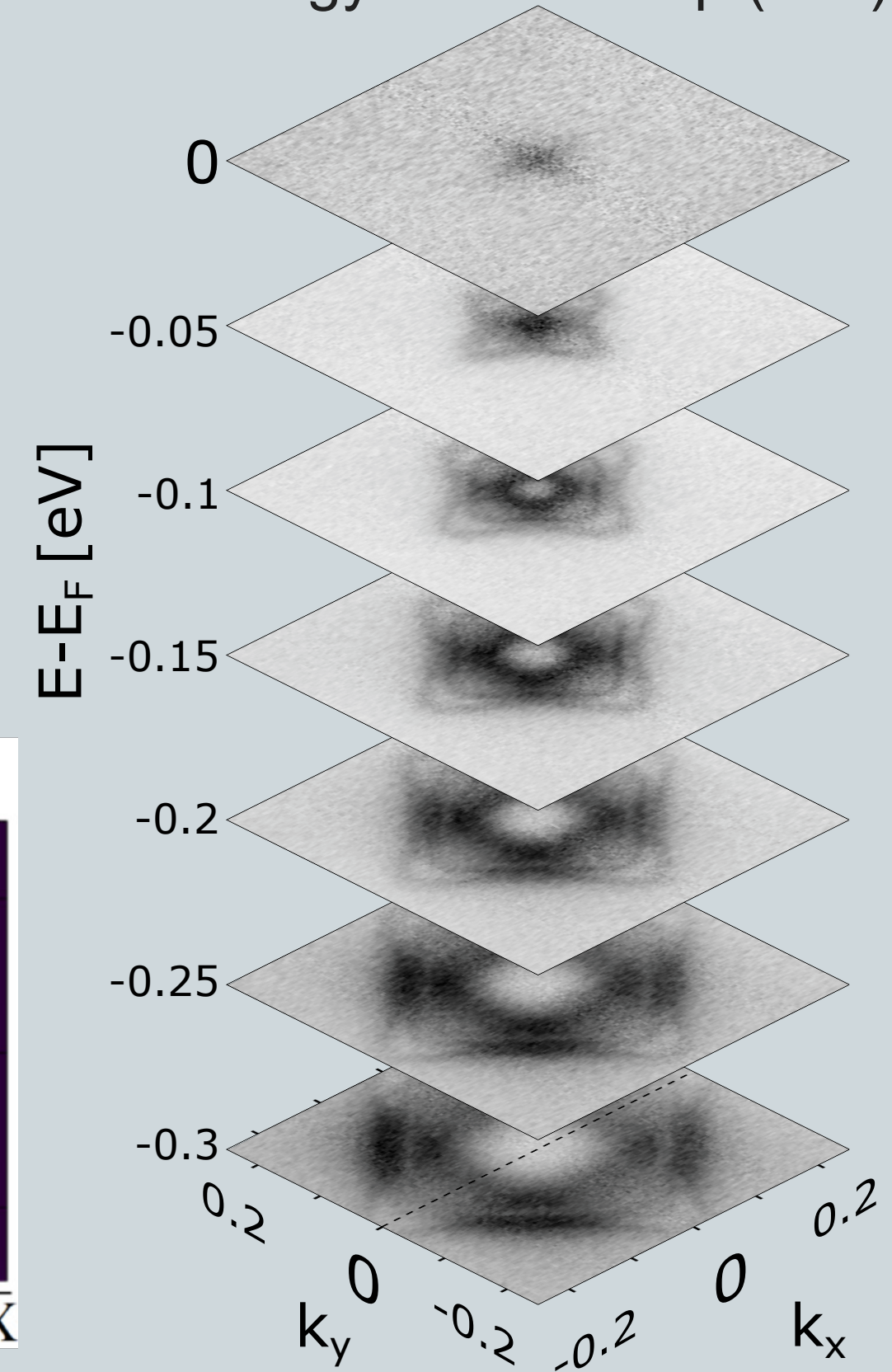


The projected surface states and corresponding Fermi surface of semi-infinite α -Sn under a compressive in-plane strain of -1% [5].

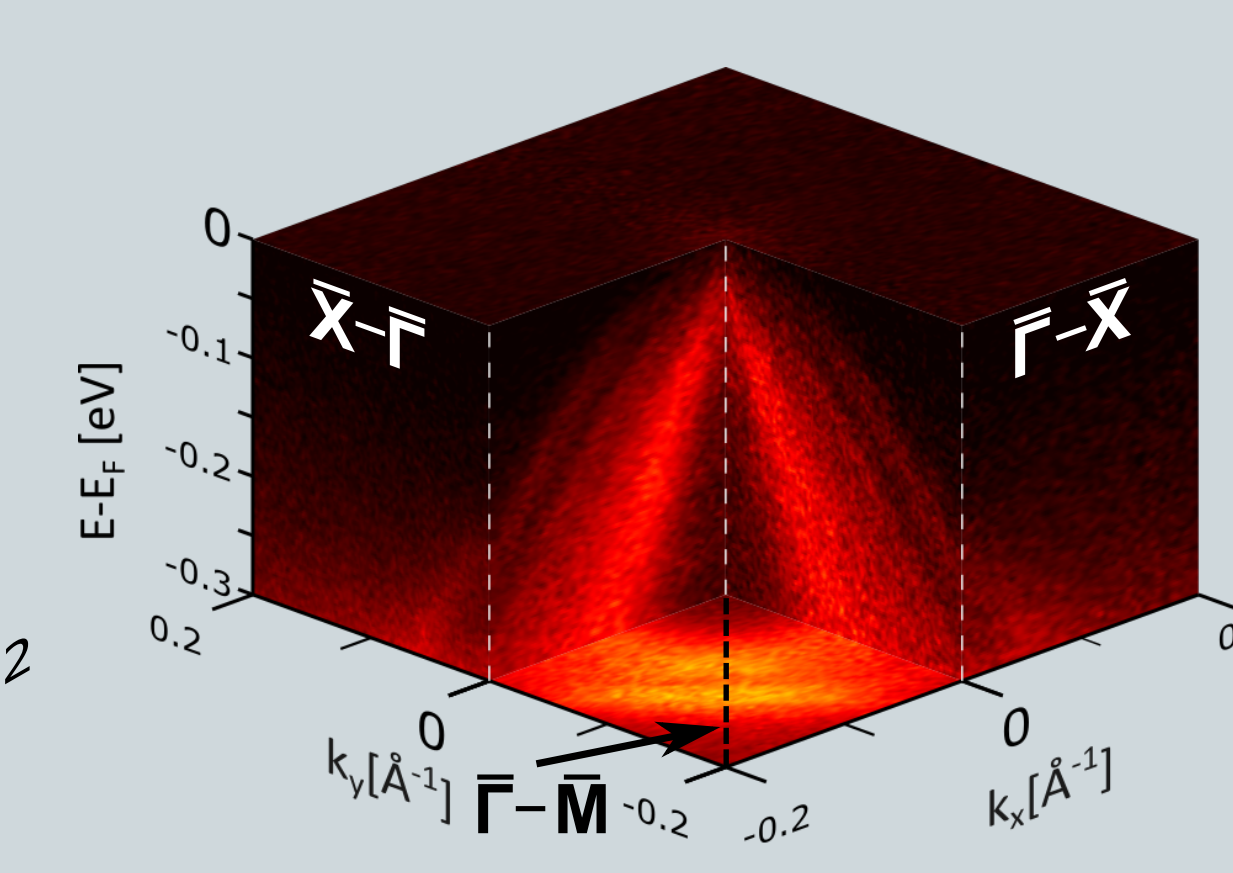
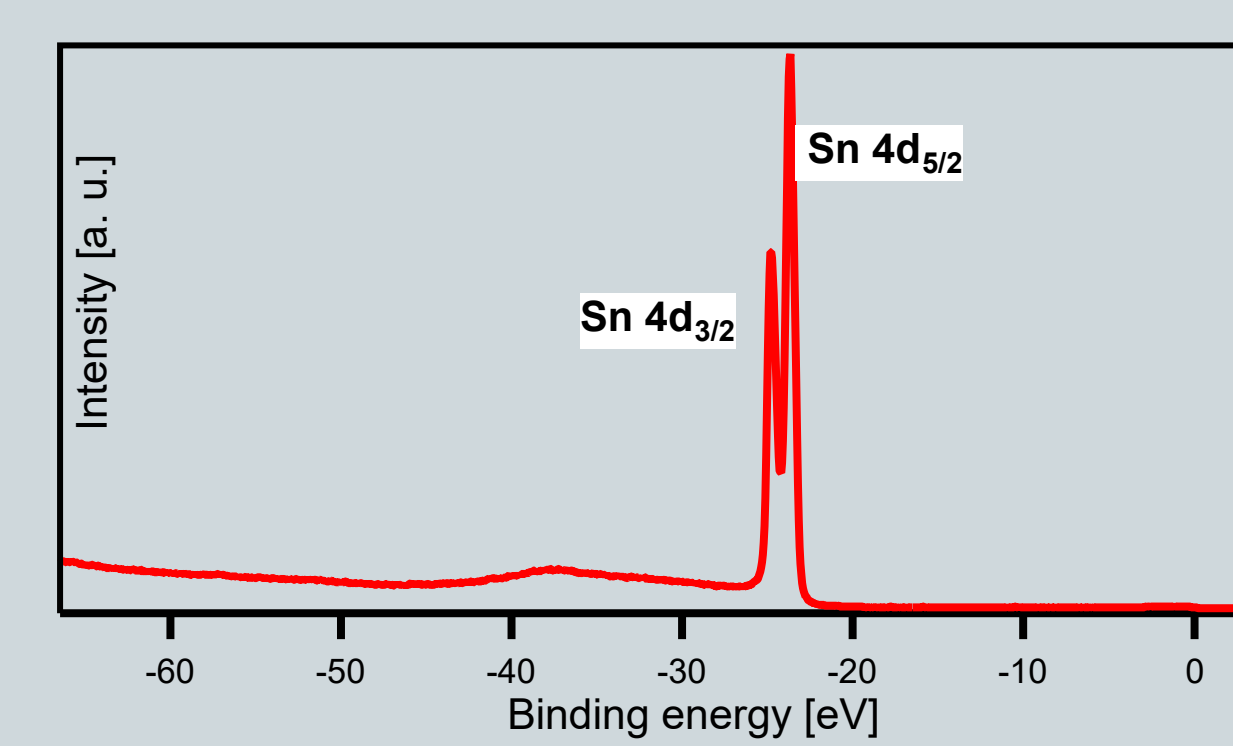


LDOS on the (001) surface for α -Sn (f) under 1% tensile strain and (i) under 1% compressive strain [1].

150nm α -Sn: Constant energy surface map (001)

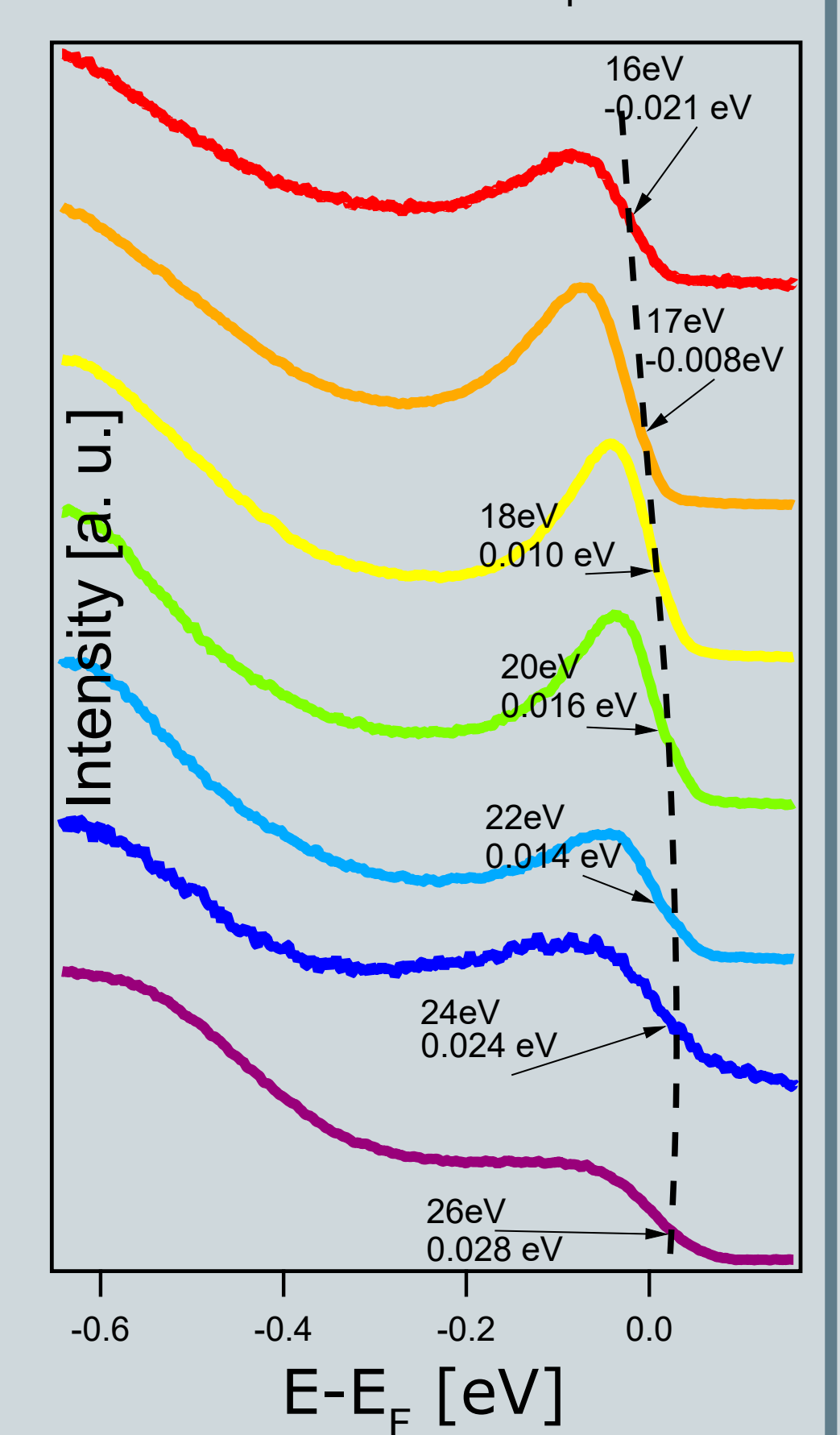


Core levels of 150nm α -Sn



3D ARPES map of 150nm α -Sn at Γ point (001)

Energy Dispersion Curves in function of E_{ph}



Summary

- Good quality grey Sn thin films obtained on semi insulating substrate shown by RHEED, AFM and XRD data.
- 0.1% compressive strain** by XRD measurements - **DSM phase** [1,5]
- ARPES spectra show **DSM phase** as predicted theoretically in [1]
- Negative longitudinal magnetoresistance (**NLMR**) - additional signature of **DSM phase** from transport measurements

ARPES spectra of grown grey Sn thin films are in agreement with theoretical predictions [1] of **DSM phase presence** for compressively strained α -Sn. Growth on hybrid insulating CdTe/GaAs substrate allowed for further transport measurements that show **NLMR** and suggests **transition of α -Sn DSM to Weyl semimetal (WSM)** under magnetic field.

α -Sn is a promising material with possible applications such as **spin charge conversion** by spin pumping or employment in high-speed electronics and **spintronics** (e.g. **spin-filter transistor** with a controllable spin polarized current) as WSM.

References

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